

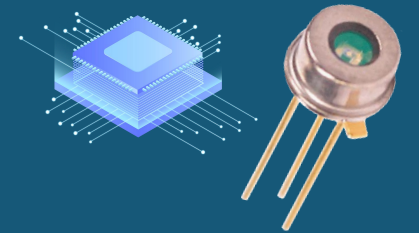
InGaAs Photodetector 5000 μ m (TO-CAN)

Features

- Bright Surface 5000 μ m
- To-5 Package
- Long Wavelength Operation
- Low Dark Current
- High Responsivity

Application

- Monitoring and Meter
- Optical Instruments
- Power Monitoring
- Test equipment



Absolute Maximum Ratings (Tc=25°C .unless otherwise specified)

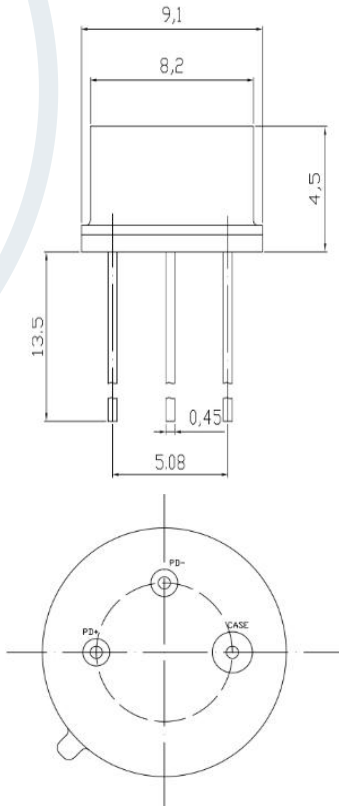
Parameter	Symbol	Min.	Max.	Unit	Test Condition
Forward Current	I _{FP}	-	10	mA	CW
Reverse Bias	V _R	-	20	V	CW
Operating Temperature	T _{OP}	-20	+70	°C	-
Storage Temperature	T _{stg}	-40	+100	°C	-
Soldering Temperature/Time	-	260/10		°C/S	-



Specifications (electrical & optical characteristics) T= 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Wavelength Range	λ	1000	-	1700	nm	-
Active Area	Φ	-	5000	-	μm	-
Saturated Optical Power	P_s	10	-	-	dBm	$V_R = 0V$
Dark Current	I_d	-	8	-	nA	$V_R = 5V$
Responsibility	Res	0.85 @ 1310nm			A / W	$\phi_e = 100 \mu\text{W}, \lambda = 1310\text{nm}$
		0.90 @ 1550nm				$\phi_e = 100 \mu\text{W}, \lambda = 1550\text{nm}$
Capacitance	C_t	-	-	280	pF@ $\Phi 5000$	$V_R = 5V, f = 1 \text{ MHz}$
Reverse Breaksown V	V_{BR}	35	-	-	v	$I_d = 10 \mu\text{A}, \phi_e = 0$
Input Power Range	P	-70	-	6	dBm	$V_R = 5V, R_L = 50\Omega$
		-60	-	16		
		-50	-	26		
		-40	-	36		

Pin Assignment

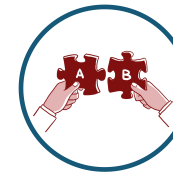


Order Information

GTA2009	(InGaAs Photo-detector	5000 μ m)
GTA2006	(InGaAs Photo-detector	2000 μ m)
GTA2007	(InGaAs Photo-detector	1000 μ m)
GTA2008	(InGaAs Photo-detector	300 μ m)
GTA2010	(InGaAs Photo-detector	10000 μ m)



Please let us know your request details before order.



Customize for you

